## **Amendments to the Claims:**

This listing of claims will replace all prior versions and listing of claims in the application.

## **Listing of Claims:**

1. - 6. (Canceled)

7. (Currently Amended) A thin film type electron emitter comprising:

a plurality of electron source elements, each of which has a structure in which a bottom electrode, an insulating layer, and a top electrode are laminated in this order, and each of which emits an electron from a surface of the top electrode when applying a positive voltage to the top electrode; and

a plurality of bus electrodes that apply a driving voltage to a top electrode of an electron source element in a first direction among the plurality of electron source elements,

wherein each of the bus electrodes comprises:

a thin film electrode that is integrated formed integrally with the top electrode; and

a thick film electrode provided on the thin film electrode, said thick film electrode having a film thickness thicker than that of the thin film electrode.

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- 8. (Original) A thin film type electron emitter according to claim 7, wherein the thick film electrode has an open area that is provided in an area where the insulting layer is formed.
- 9. (Previously Presented) A thin film type electron emitter according to claim 7, wherein the thick film electrode is a metallic layer that is formed by any of plating, vacuum evaporation, chemical vapor deposition, and printing.

10. - 20. (Canceled)

21. (Previously Presented) A method of manufacturing a thin film type electron emitter comprising: a plurality of electron source elements, each of which has a structure in which a bottom electrode, an insulating layer, and a top electrode are laminated in this order, and each of which emits an electron from a surface of the top electrode when applying positive voltage to the top electrode; and a plurality of bus electrodes comprising a thin film electrode integrated with the top electrode, and a thick film electrode that is provided on the thin film electrode, and that has a film thickness thicker than that of the thin film electrode, said plurality of bus electrodes applying driving voltage to a top electrode of an electron source element in a first direction among the plurality of electron source elements,

said method comprising:

forming the bottom electrode;

forming the insulating layer;

forming a thin conductive film on the bottom electrode and the insulating layer; selectively forming a thick film electrode on the thin conductive film by plating or printing; and

forming the thin film electrode and the top electrode by selectively patterning the thin conductive film.

- 22. (Currently Amended) A method of manufacturing a thin film type electron emitter according to claim 21, wherein in the step 4 of when selectively forming the thick film electrode, an open area where the insulating layer is exposed is formed in the thick film electrode.
- 23. (Previously Presented) A method of manufacturing a thin film type electron emitter according to claim 21, wherein the thin film electrode comprises a tungsten film.
- 24. 29. (Canceled)
- 30. (Currently Amended) A display device comprising:
  - a first substrate including:
- a plurality of electron source elements, each of which has a structure in which a bottom electrode, an insulating layer, and a top electrode are laminated in this

order, and each of which emits an electron from a surface of the top electrode when applying positive voltage to the top electrode; and

a plurality of bus electrodes that apply a driving voltage to a top electrode of an electron source element in a first direction among the plurality of electron source elements;

a frame glass; and

a second substrate having phosphor;

wherein a space surrounded by the first substrate, the frame glass, and the second substrate is allowed to be a vacuum atmosphere; and

wherein each bus electrode of the first substrate comprises:

a thin film electrode that is integrated formed integrally with the top electrode; and

a thick film electrode provided on the thin film electrode, said thick film electrode being thicker than the thin film electrode, and said thick film electrode.

- 31. (Original) A display device according to claim 30, wherein the thick film electrode has an open area that is provided in an area where the insulating layer is formed.
- 32. (Previously Presented) A display device according to claim 30, wherein the thick film electrode is a metallic layer that is formed by any of plating, vacuum evaporation, chemical vapor deposition, and printing.

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- 33. (New) A thin film type electron emitter according to claim 7, wherein the thick film electrode has a same material as a top surface of said thin film electrode and is formed by selectively growing on the thin film electrode by electroplating.
- 34. (New) A method of manufacturing a thin film type electron emitter according to claim 21, wherein the thick film electrode has a same material as a top surface of said thin film electrode and is formed by selectively growing on the thin film electrode by electroplating.
- 35. (New) A display device according to claim 30, wherein the thick film electrode has a same material as a top surface of said thin film electrode and is formed by selectively growing on the thin film electrode by electroplating.